Silicon PNP Epitaxial

HITACHI

Application • Low frequency low noise amplifier • Complementary pair with 2SC1775/A **Outline** TO-92 (1) 1. Emitter 2. Collector 3. Base



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

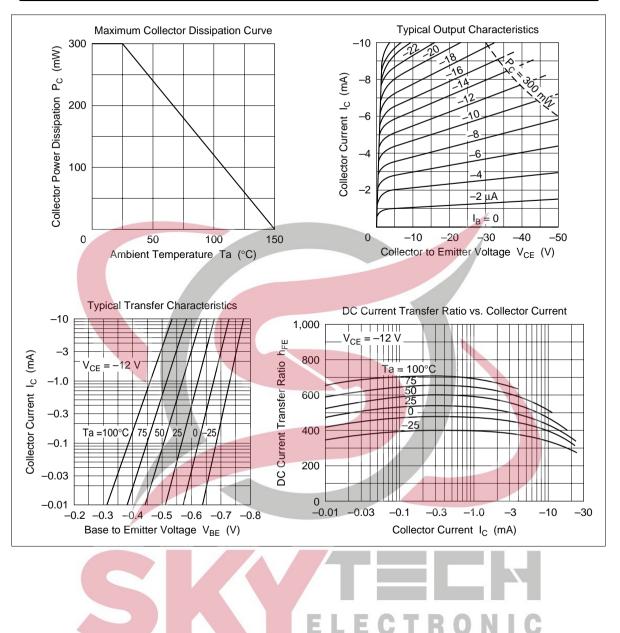
Item	Symbol	2SA872	2SA872A	Unit
Collector to base voltage	V _{CBO}	-90	-120	V
Collector to emitter voltage	V _{CEO}	-90	-120	V
Emitter to base voltage	V _{EBO}	-5	-5	V
Collector current	I _c	-50	-50	mA
Collector power dissipation	Pc	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-50 to +150	°C

Electrical Characteristics (Ta = 25°C)

		2SA872 2SA872A							
Item	Symbol	Min	Тур	Max	Min	Тур	Мах	Unit	Test conditions
Collector to emitter breakdown voltage	V _{(BR)CEO}	-90			-120	-	-	V	$I_c = -1 \text{ mA}, \text{ R}_{BE} = \infty$
Collector cutoff current	I _{CBO}	_	_	-0.5	-	-	-	μΑ	$V_{CB} = -75 \text{ V}, \text{ I}_{E} = 0$
		—		_	_	_	-0.5	μA	$V_{ce} = -100 \text{ V}, I_e = 0$
DC current tarnsfer ratio	h _{FE1} *1	250	-	800	250	-	800		$V_{CE} = -12 V,$ $I_{c} = -2 mA$
	h _{FE2}	160	-		160	-	-		$V_{ce} = -12 V,$ $I_c = -0.1 mA$
Base to emitter voltage	V _{BE}	_	-	-0.75	_	_	-0.75	V	$V_{CE} = -12 \text{ V},$ $I_{c} = -2 \text{ mA}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	-0.5	_		-0.5	V	$I_{c} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}$
Gain bandwidth product	f _T	-7	120	-7	-	120	-	MHz	$V_{CE} = -12 V,$ $I_{c} = -2 mA$
Collector output capacitance	Cob	-	1.8	T E	īū	1.8 E C	Τr	pF	$V_{CB} = -25 \text{ V}, I_E = 0,$ f = 1 MHz
Noise figure	NF	_		5.0	_	_	5.0	dB	$\label{eq:V_ce} \begin{split} V_{ce} &= -6 \ V, \ f = 10 \ Hz \\ I_c &= -50 \ \mu A \\ R_g &= 50 \ k\Omega \end{split}$
		_		1.5	_	_	1.5	dB	f = 1 kHz
Note: 1. The 2SA872	/A is group	ed by h	n _{FE1} as f	ollows.					

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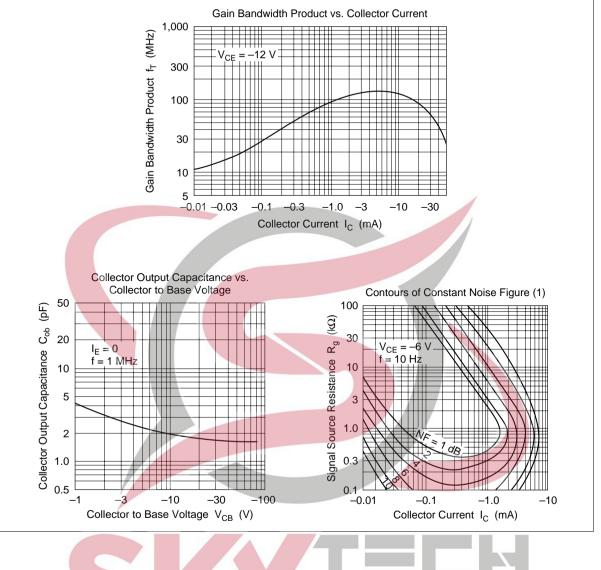
250 to 500 400 to 800



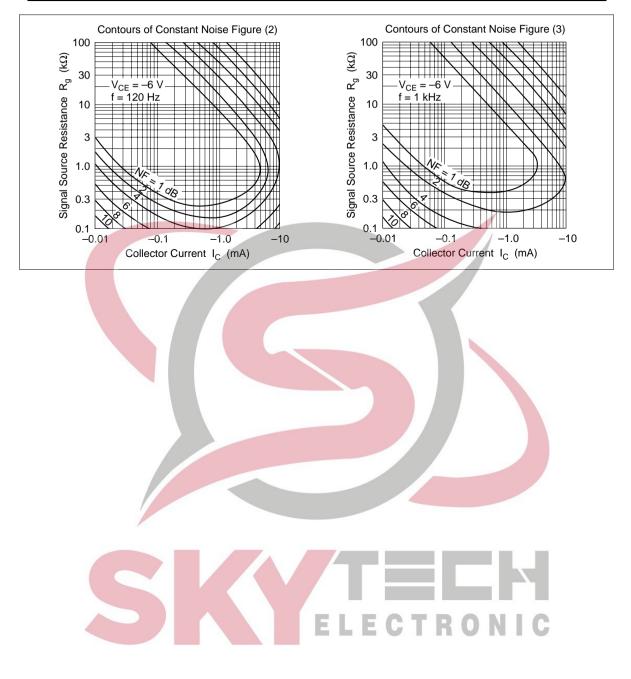
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2

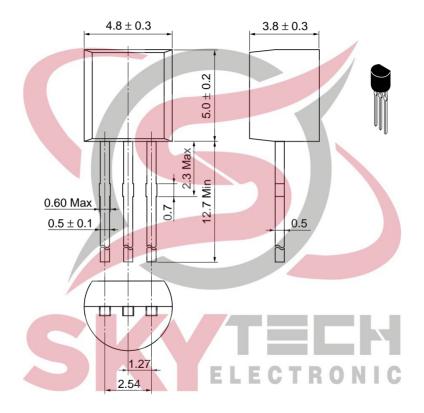
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SKELECTRONIC



Unit: mm



Hitachi Code TO-92 (1) JEDEC Conforms

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